

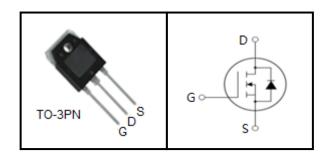
500V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information			
Device	Package	Marking	
TMV28N50H	TO-3PN	V28N50H	



Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	500	V
Continuous Drain Current	I _D	28	Α
Pulsed Drain Current (note1)	I _{DM}	112	Α
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulse Avalanche Energy (note2)	E _{AS}	1350	mJ
Avalanche Current (note1)	I _{AR}	16	Α
Repetitive Avalanche Energy (note1)	E _{AR}	90	mJ
Power Dissipation (T _C = 25°C)	P _D	150	W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	ô

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	0.85	°C/W	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	60	30/00	



Specifications $T_J = 25^{\circ}$ C, unless otherwise noted						
Parameter	Symbol	7 .	Value			
		Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	500			V
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 500V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D = 14A		0.16	0.2	Ω
Dynamic				•		
Input Capacitance	C _{iss}	V 0V		4550		pF
Output Capacitance	C _{oss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		440		
Reverse Transfer Capacitance	C _{rss}	f = 1.0MHz		60		
Total Gate Charge	Q_g			120		nC
Gate-Source Charge	Q_{gs}	$V_{DD} = 400V, I_{D} = 28A,$ $V_{GS} = 10V$		18		
Gate-Drain Charge	Q_{gd}	65		51		
Turn-on Delay Time	t _{d(on)}	$V_{DD} = 250V, I_{D} = 28A,$ $R_{G} = 25 \Omega$		40		
Turn-on Rise Time	t _r			70		ns
Turn-off Delay Time	t _{d(off)}			180		
Turn-off Fall Time	t _f			90		
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T			28	Δ
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			112	A
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 28\text{A}, V_{GS} = 0\text{V}$			1.4	V
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 28A,$		480		ns
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /μs		8		μC

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. I_{AS} = 16A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 ^{o}C
- 3. Pulse Test: Pulse width ≤ 350µs, Duty Cycle ≤ 1%

ID, Drain Current (A)

Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^{\circ}C$)

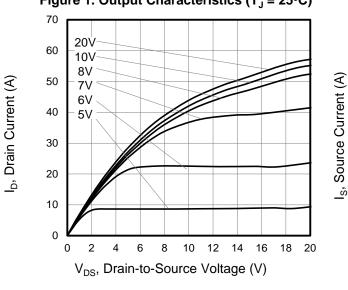


Figure 2. Body Diode Forward Voltage

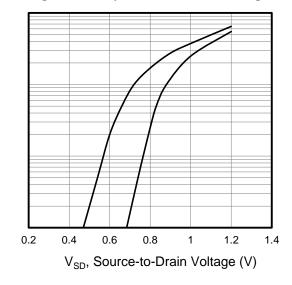


Figure 3. Drain Current vs. Temperature

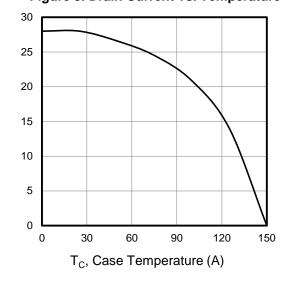


Figure 4. BV_{DSS} Variation vs. Temperature

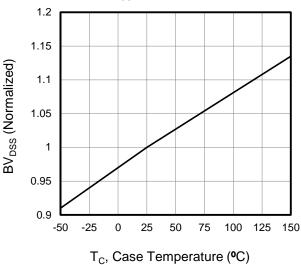


Figure 5. Transfer Characteristics

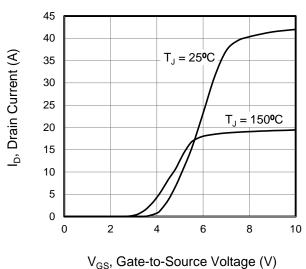
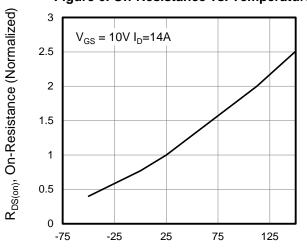
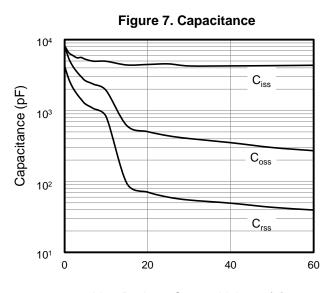


Figure 6. On-Resistance vs. Temperature



T_J, Junction Temperature (°C)

Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted



 V_{DS} , Drain-to-Source Voltage (V)

Figure 8. Gate Charge 12 $V_{DD} = 100V$ V_{GS}, Gate-to-Source Voltage (V) 10 $V_{DD} = 250V$ $V_{DD} = 400V$ 8 6 4 2 0 30 0 60 90 120 150

Q_q, Total Gate Charge (nC)

Figure 9. Transient Thermal Impedance

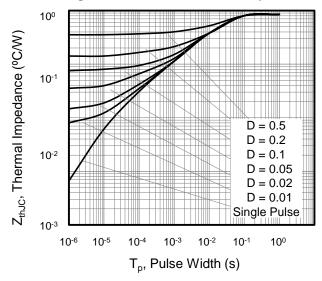


Figure A: Gate Charge Test Circuit and Waveform

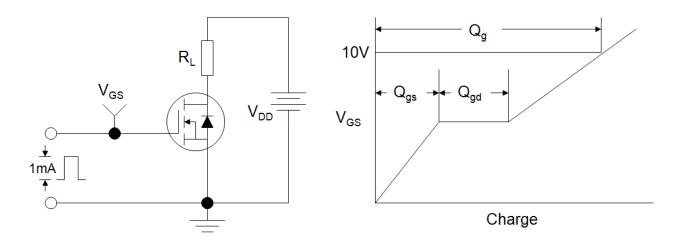


Figure B: Resistive Switching Test Circuit and Waveform

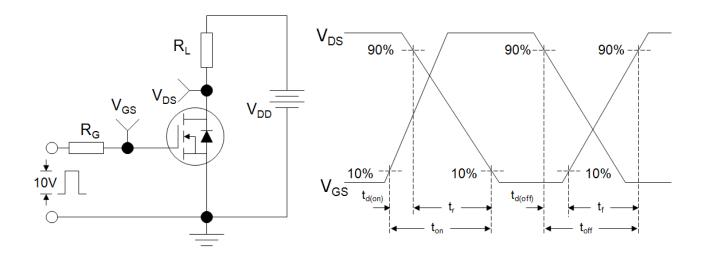
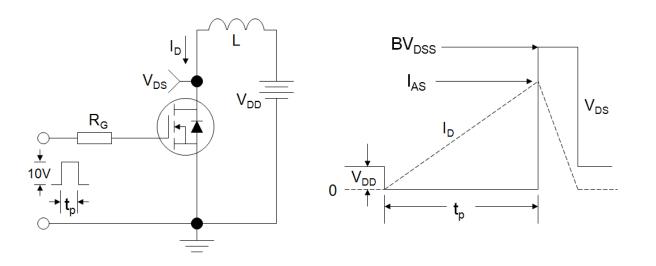
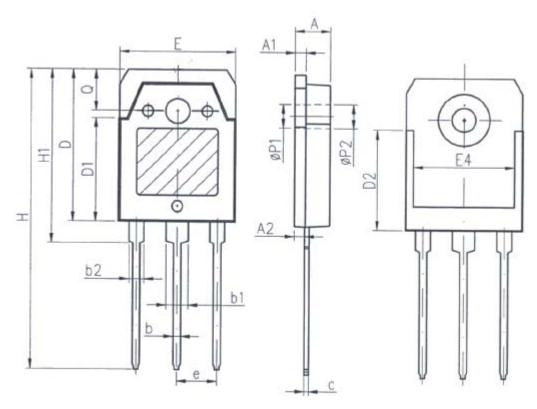


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-3PN



Unit:mm			
Symbol	Min.	Max.	
Α	4. 6	5	
A1	1. 4	1. 65	
A2	1. 18	1. 58	
b	0.8	1. 2	
b1	2. 8	3. 2	
b2	1.8	2. 2	
С	0.5	0. 75	
D	19. 6	20. 2	
D1	13. 55	14. 25	
D2	12. 9REF		
E	15. 35	15. 85	
E4	12. 6	-	
е	5. 45TYP		
Н	40. 1	40. 9	
H1	23. 15	23. 65	
P1	3. 2REF		
P2	3. 5REF		



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